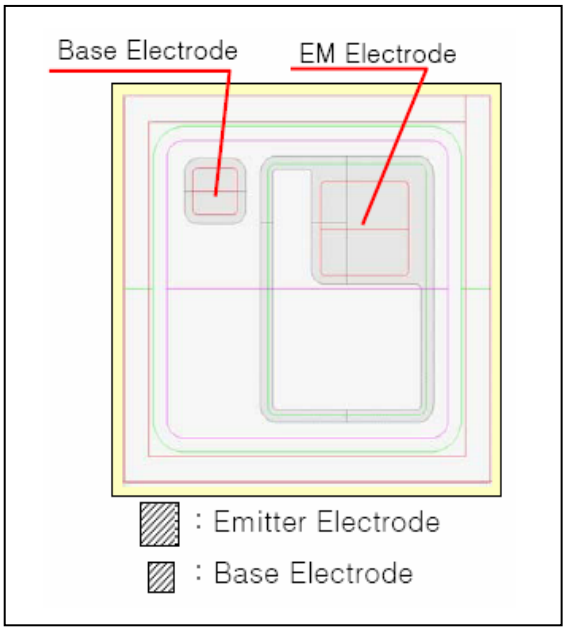
OPB0422

Silicon Photo Transistor



1. Structure

1.1 Chip Size : 0.415mm X 0.415mm

1.2 Chip thickness : 180±15um

1.3 Metallization : Top - Al, Bottom - Au

1.4 Passivation : Silicon Nitride

1.5 Bonding Pad Size

- Emitter : 138um X 138um
- Base : 70um X 70um

2. Guaranteed Probed Electrical Characteristics

(Ta=25℃)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
C-E Leakage Current	I_{CEO}			50	nA	V_{ce}=20V
Spectrum Sensitivity	λ	500		1,050	nm	
Peak Sensing Wavelength	λp		880		nm	
C-E Voltage	BV_{CEO}	90			V	I_{CE}=500uA
C-B Voltage	BV_{CBO}	100			V	I_{CB}=50uA
E-B Voltage	BV_{EBO}	6.7			V	I_{EB}=50uA
E-C Voltage	BV_{ECO}	7.1			V	I_{EC}=50uA
C-E Saturation Voltage	V_{CES}			200	mV	I_C=5mA, I_B=1mA
DC Current Gain	h_{FE}	700		1,500	-	V_{CE}=10V, Ic=1mA

3. Absolute Maximum Ratings

(Ta=25℃)

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	90	V
Emitter-Collector Voltage	V_{ECO}	7.1	V

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